

K6R4008C1A-C, K6R4008C1A-E, K6R4008C1A-I CMOS SRAM

Document Title

512Kx8 Bit High Speed Static RAM(5V Operating), Revolutionary Pin out.
Operated at Commercial, Extended and Industrial Temperature Ranges.

Revision History

RevNo.	History	Draft Data	Remark																					
Rev. 0.0	Initial release with Design Target.	Jun. 14th, 1996	Design Target																					
Rev. 0.5	Release to Preliminary Data Sheet. 0.1. Replace Design Target to Preliminary. 0.2. Delete 12ns part but add 17ns part. 0.3. Relax D.C and A.C parameters and insert new parameter(lcc1) with the test condition. 0.3.1. Insert lcc1 parameter with the test condition as address is increased with binary count. 0.3.2. Relax D.C and A.C parameters. <table><tr><td>Items</td><td>Previous spec. (15/ - /20ns part)</td><td>Relaxed spec. (15/17/20ns part)</td></tr><tr><td>lcc</td><td>190/ - /180mA</td><td>220/215/210mA</td></tr><tr><td>tcw</td><td>10/ - /12ns</td><td>12/13/14ns</td></tr><tr><td>tAW</td><td>10/ - /12ns</td><td>12/13/14ns</td></tr><tr><td>tWP($\overline{OE}=H$)</td><td>10/ - /12ns</td><td>12/13/14ns</td></tr><tr><td>tWP1($\overline{OE}=L$)</td><td>12/ - /14ns</td><td>15/17/20ns</td></tr><tr><td>tdw</td><td>7/ - /9ns</td><td>8/ 9/10ns</td></tr></table>	Items	Previous spec. (15/ - /20ns part)	Relaxed spec. (15/17/20ns part)	lcc	190/ - /180mA	220/215/210mA	tcw	10/ - /12ns	12/13/14ns	tAW	10/ - /12ns	12/13/14ns	tWP($\overline{OE}=H$)	10/ - /12ns	12/13/14ns	tWP1($\overline{OE}=L$)	12/ - /14ns	15/17/20ns	tdw	7/ - /9ns	8/ 9/10ns	Sep. 16th, 1996	Preliminary
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Rev. 1.0	Release to Final Data Sheet. 1.1. Delete Preliminary. 1.2. Delete lcc1 parameter with the test condition. 1.3. Update D.C parameters. <table><tr><td>Items</td><td>Previous spec. (15/17/20ns part)</td><td>Updated spec. (15/17/20ns part)</td></tr><tr><td>lcc</td><td>220/215/210mA</td><td>170/165/160mA</td></tr></table> 1.4. Add the test condition for VOH1 with Vcc=5V±5% at 25°C. 1.5. Add timing <u>diagram</u> to define tWP as "(Timing Wave Form of Write Cycle(CS=Low fixed)".	Items	Previous spec. (15/17/20ns part)	Updated spec. (15/17/20ns part)	lcc	220/215/210mA	170/165/160mA	Jun. 5th, 1997	Final															
Items	Previous spec. (15/17/20ns part)	Updated spec. (15/17/20ns part)																						
lcc	220/215/210mA	170/165/160mA																						
Rev. 2.0	2.1 Add extended and industrial temperature range parts.	Jun. 5th, 1997	Final																					

The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions on the parameters of this device. If you have any questions, please contact the SAMSUNG branch office near your office, call or contact Headquarters.



ELECTRONICS

K6R4008C1A-C, K6R4008C1A-E, K6R4008C1A-I CMOS SRAM

512K x 8 Bit High-Speed CMOS Static RAM

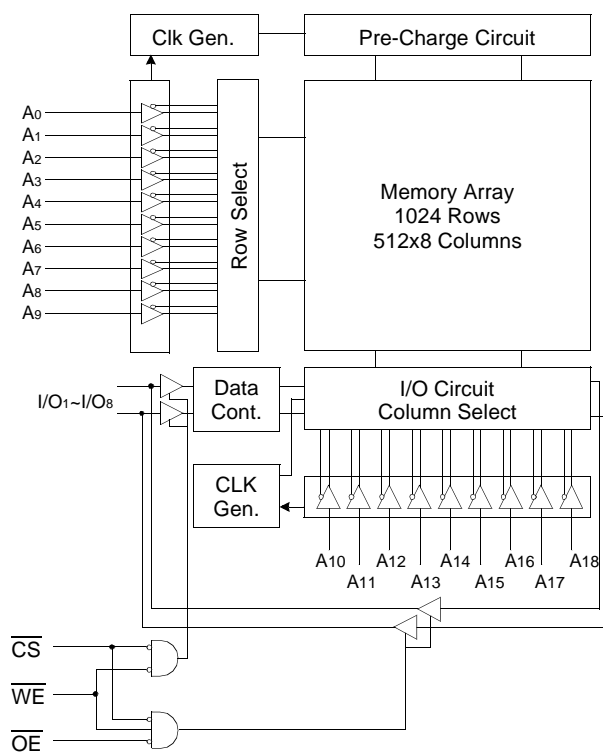
FEATURES

- Fast Access Time 15,17,20ns(Max.)
- Low Power Dissipation
 - Standby (TTL) : 50mA(Max.)
 - (CMOS) : 10mA(Max.)
 - Operating K6R4008C1A-15 : 170mA(Max.)
 - K6R4008C1A-17 : 165mA(Max.)
 - K6R4008C1A-20 : 160mA(Max.)
- Single 5.0V±10% Power Supply
- TTL Compatible Inputs and Outputs
- I/O Compatible with 3.3V Device
- Fully Static Operation
 - No Clock or Refresh required
- Three State Outputs
- Center Power/Ground Pin Configuration
- Standard Pin Configuration
 - K6R4008C1A-J : 36-SOJ-400

ORDERING INFORMATION

K6R4008C1A-C15/C17/C20	Commercial Temp.
K6R4008C1A-E15/E17/E20	Extended Temp.
K6R4008C1A-I15/I17/I20	Industrial Temp.

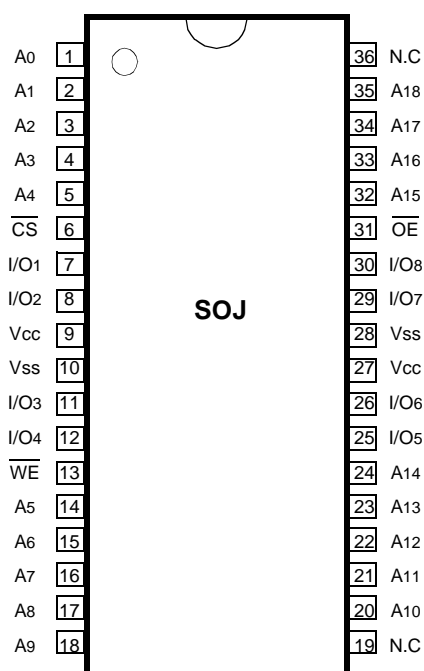
FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The K6R4008C1A is a 4,194,304-bit high-speed Static Random Access Memory organized as 524,288 words by 8 bits. The K6R4008C1A uses 8 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. The device is fabricated using SAMSUNG's advanced CMOS process and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications. The K6R4008C1A is packaged in a 400mil 36-pin plastic SOJ.

PIN CONFIGURATION (Top View)



PIN FUNCTION

Pin Name	Pin Function
A0 - A18	Address Inputs
\overline{WE}	Write Enable
\overline{CS}	Chip Select
\overline{OE}	Output Enable
I/O1 ~ I/O8	Data Inputs/Outputs
Vcc	Power(+5.0V)
Vss	Ground
N.C	No Connection

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ABSOLUTE MAXIMUM RATINGS*

Parameter		Symbol	Rating	Unit
Voltage on Any Pin Relative to V _{SS}		V _{IN} , V _{OUT}	-0.5 to 7.0	V
Voltage on V _{CC} Supply Relative to V _{SS}		V _{CC}	-0.5 to 7.0	V
Power Dissipation		P _D	1.0	W
Storage Temperature		T _{STG}	-65 to 150	°C
Operating Temperature	Commercial	T _A	0 to 70	°C
	Extended	T _A	-25 to 85	°C
	Industrial	T _A	-40 to 85	°C

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS*(T_A=0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
Ground	V _{SS}	0	0	0	V
Input High Voltage	V _{IH}	2.2	-	V _{CC} +0.5***	V
Input Low Voltage	V _{IL}	-0.5**	-	0.8	V

* The above parameters are also guaranteed at extended and industrial temperature ranges.

** V_{IL}(Min) = -2.0V a.c(Pulse Width ≤ 10ns) for I ≤ 20mA.

*** V_{IH}(Max) = V_{CC} + 2.0V a.c (Pulse Width ≤ 10ns) for I ≤ 20mA.

DC AND OPERATING CHARACTERISTICS*(T_A=0 to 70°C, V_{CC}=5.0V±10%, unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Max	Unit
Input Leakage Current	I _{LI}	V _{IN} =V _{SS} to V _{CC}		-2	2	μA
Output Leakage Current	I _{LO}	CS=V _{IH} or OE=V _{IH} or WE=V _{IL} V _{OUT} =V _{SS} to V _{CC}		-2	2	μA
Operating Current	I _{CC}	Min. Cycle, 100% Duty CS=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	15ns	-	170	mA
			17ns	-	165	
			20ns	-	160	
Standby Current	I _{SB}	Min. Cycle, CS=V _{IH}		-	50	mA
	I _{SB1}	f=0MHz, CS≥V _{CC} -0.2V, V _{IN} ≥V _{CC} -0.2V or V _{IN} ≤0.2V		-	10	
Output Low Voltage Level	V _{OL}	I _{OL} =8mA		-	0.4	V
Output High Voltage Level	V _{OH}	I _{OH} =-4mA		2.4	-	V

* The above parameters are also guaranteed at extended and industrial temperature ranges.

CAPACITANCE*(T_A=25°C, f=1.0MHz)

Item	Symbol	Test Conditions	MIN	Max	Unit
Input/Output Capacitance	C _{I/O}	V _{I/O} =0V	-	8	pF
Input Capacitance	C _{IN}	V _{IN} =0V	-	7	pF

* Capacitance is sampled and not 100% tested.

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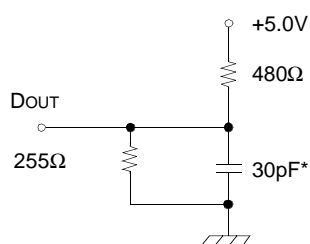
AC CHARACTERISTICS($T_A=0$ to 70°C , $V_{CC}=5.0\text{V}\pm 10\%$, unless otherwise noted.)

TEST CONDITIONS*

Parameter	Value
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3ns
Input and Output timing Reference Levels	1.5V
Output Loads	See below

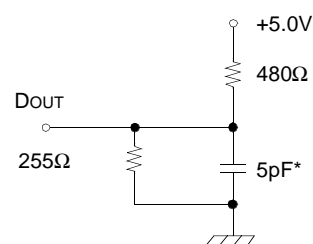
* The above parameters are also guaranteed at extended and industrial temperature ranges.

Output Loads(A)



Output Loads(B)

for tHZ, tLZ, tWHZ, tOW, tOLZ & tOHZ



* Including Scope and Jig Capacitance

READ CYCLE*

Parameter	Symbol	K6R4008C1A-15		K6R4008C1A-17		K6R4008C1A-20		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	15	-	17	-	20	-	ns
Address Access Time	t _{AA}	-	15	-	17	-	20	ns
Chip Select to Output	t _{CO}	-	15	-	17	-	20	ns
Output Enable to Valid Output	t _{OE}	-	7	-	8	-	9	ns
Chip Enable to Low-Z Output	t _{LZ}	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	t _{OLZ}	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	t _{HZ}	0	7	0	8	0	9	ns
Output Disable to High-Z Output	t _{OHZ}	0	7	0	8	0	9	ns
Output Hold from Address Change	t _{OH}	3	-	3	-	3	-	ns
Chip Selection to Power Up Time	t _{PU}	0	-	0	-	0	-	ns
Chip Selection to Power Down Time	t _{PD}	-	15	-	17	-	20	ns

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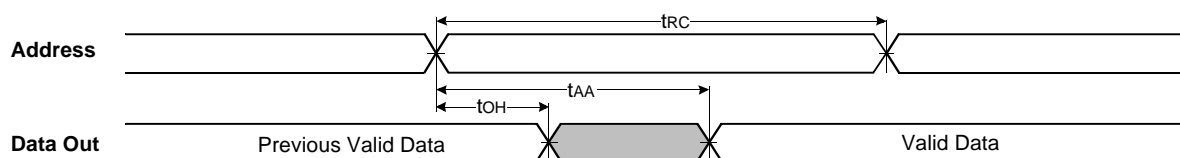
WRITE CYCLE*

Parameter	Symbol	K6R4008C1A-15		K6R4008C1A-17		K6R4008C1A-20		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	15	-	17	-	20	-	ns
Chip Select to End of Write	t _{CW}	12	-	13	-	14	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	0	-	ns
Address Valid to End of Write	t _{AW}	12	-	13	-	14	-	ns
Write Pulse Width($\overline{\text{OE}}$ High)	t _{WP}	12	-	13	-	14	-	ns
Write Pulse Width($\overline{\text{OE}}$ Low)	t _{WP1}	15	-	17	-	20	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	0	-	ns
Write to Output High-Z	t _{WHZ}	0	7	0	8	0	9	ns
Data to Write Time Overlap	t _{DW}	8	-	9	-	10	-	ns
Data Hold from Write Time	t _{DH}	0	-	0	-	0	-	ns
End Write to Output Low-Z	t _{OW}	3	-	3	-	3	-	ns

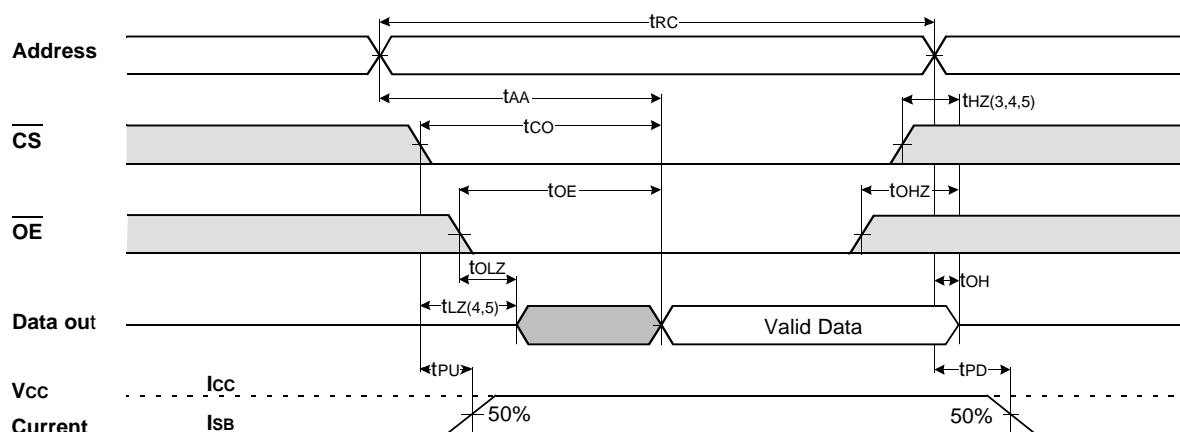
* The above parameters are also guaranteed at extended and industrial temperature ranges.

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{\text{CS}}=\overline{\text{OE}}=V_{\text{IL}}$, $\overline{\text{WE}}=V_{\text{IH}}$)



TIMING WAVEFORM OF READ CYCLE(2) ($\overline{\text{WE}}=V_{\text{IH}}$)

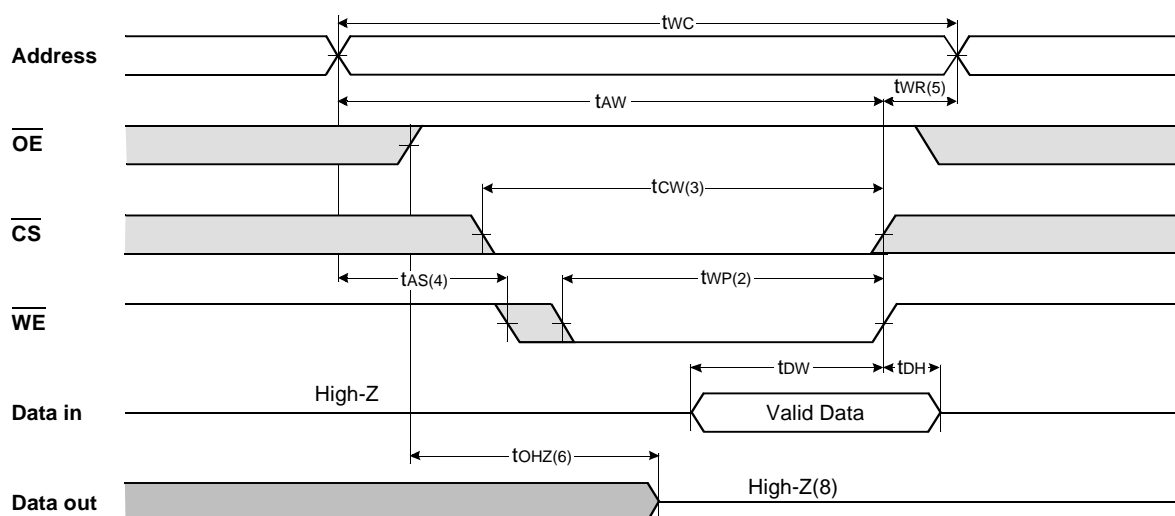


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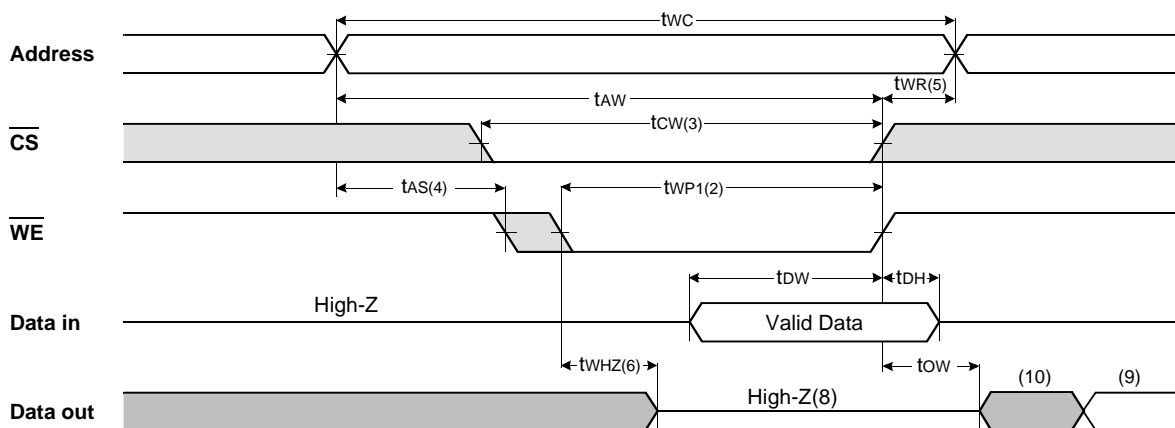
NOTES(READ CYCLE)

1. \overline{WE} is high for read cycle.
2. All read cycle timing is referenced from the last valid address to the first transition address.
3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device.
5. Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with $\overline{CS}=V_{IL}$.
7. Address valid prior to coincident with \overline{CS} transition low.
8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.

TIMING WAVEFORM OF WRITE CYCLE(1) (\overline{OE} = Clock)

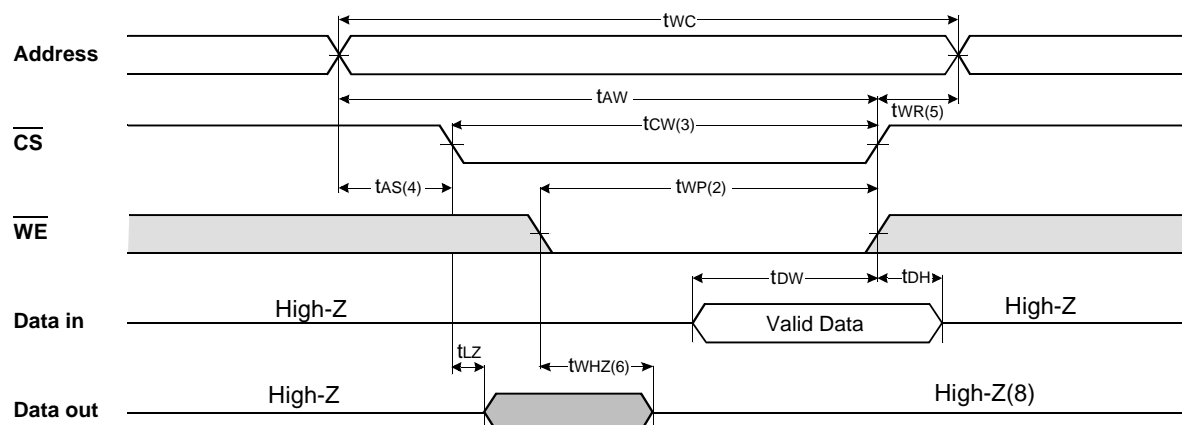


TIMING WAVEFORM OF WRITE CYCLE(2) (\overline{OE} =Low Fixed)



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TIMING WAVEFORM OF WRITE CYCLE(3) (\overline{CS} = Controlled)



NOTES(WRITE CYCLE)

1. All write cycle timing is referenced from the last valid address to the first transition address.
2. A write occurs during the overlap of a low \overline{CS} and \overline{WE} . A write begins at the latest transition \overline{CS} going low and \overline{WE} going low ; A write ends at the earliest transition \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of \overline{CS} going low to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as \overline{CS} or \overline{WE} going high.
6. If \overline{OE} , \overline{CS} and \overline{WE} are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If \overline{CS} goes low simultaneously with \overline{WE} going or after \overline{WE} going low, the outputs remain high impedance state.
9. Dout is the read data of the new address.
10. When \overline{CS} is low : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

FUNCTIONAL DESCRIPTION

\overline{CS}	\overline{WE}	\overline{OE}	Mode	I/O Pin	Supply Current
H	X	X*	Not Select	High-Z	I_{SB} , I_{SB1}
L	H	H	Output Disable	High-Z	I_{CC}
L	H	L	Read	DOUT	I_{CC}
L	L	X	Write	DIN	I_{CC}

* X means Don't Care.

CMOS SRAM

Units:millimeters/Inches

The drawing shows a rectangular component with dimensions and tolerances. The top view shows a width of 11.18 ± 0.12 and a height of 0.440 ± 0.005 . The side view shows a thickness of 10.16 ± 0.400 and a height of 9.40 ± 0.25 . The bottom view shows a width of 23.90 ± 0.941 and a height of 0.925 ± 0.005 . The bottom view also shows a width of 0.43 ± 0.10 and a height of 0.017 ± 0.004 . The bottom view also shows a width of 1.27 ± 0.050 and a height of 0.71 ± 0.10 . The bottom view also shows a width of 0.95 ± 0.0375 and a height of 0.028 ± 0.004 . The bottom view also shows a width of 0.017 ± 0.004 and a height of 0.008 ± 0.004 . The bottom view also shows a width of 0.20 ± 0.10 and a height of 0.008 ± 0.004 . The bottom view also shows a width of 0.69 ± 0.027 and a height of 0.008 ± 0.004 . The bottom view also shows a width of 0.940 ± 0.010 and a height of 0.008 ± 0.004 . The bottom view also shows a width of 0.940 ± 0.010 and a height of 0.008 ± 0.004 .